

Silicon PNP Power Transistors

2SA1308

DESCRIPTION

- With TO-220F package
- Low collector saturation voltage

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

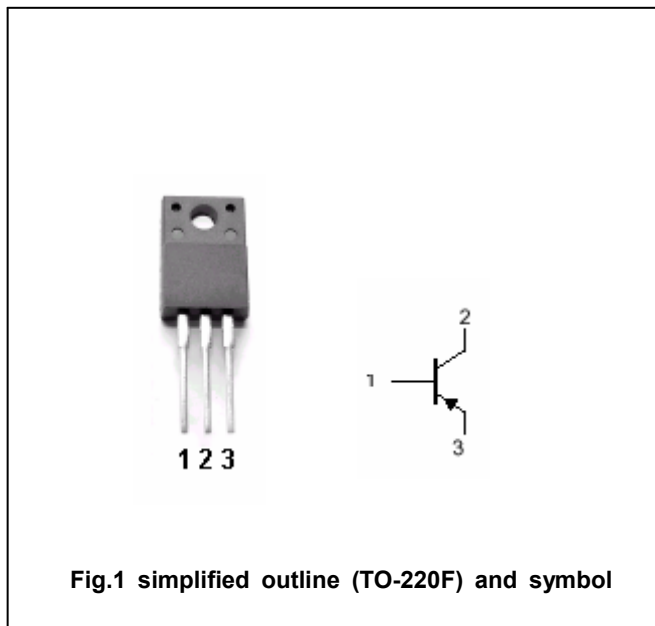


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-5	A
I _{CM}	Collector current-peak		-8	A
P _C	Collector dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A;I _B =-0.15A			-0.4	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3A;I _B =-0.15A			-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V;I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-1V	70		240	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-1V	30			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-4V		60		MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-10V;f=1MHz		200		pF

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PACKAGE OUTLINE

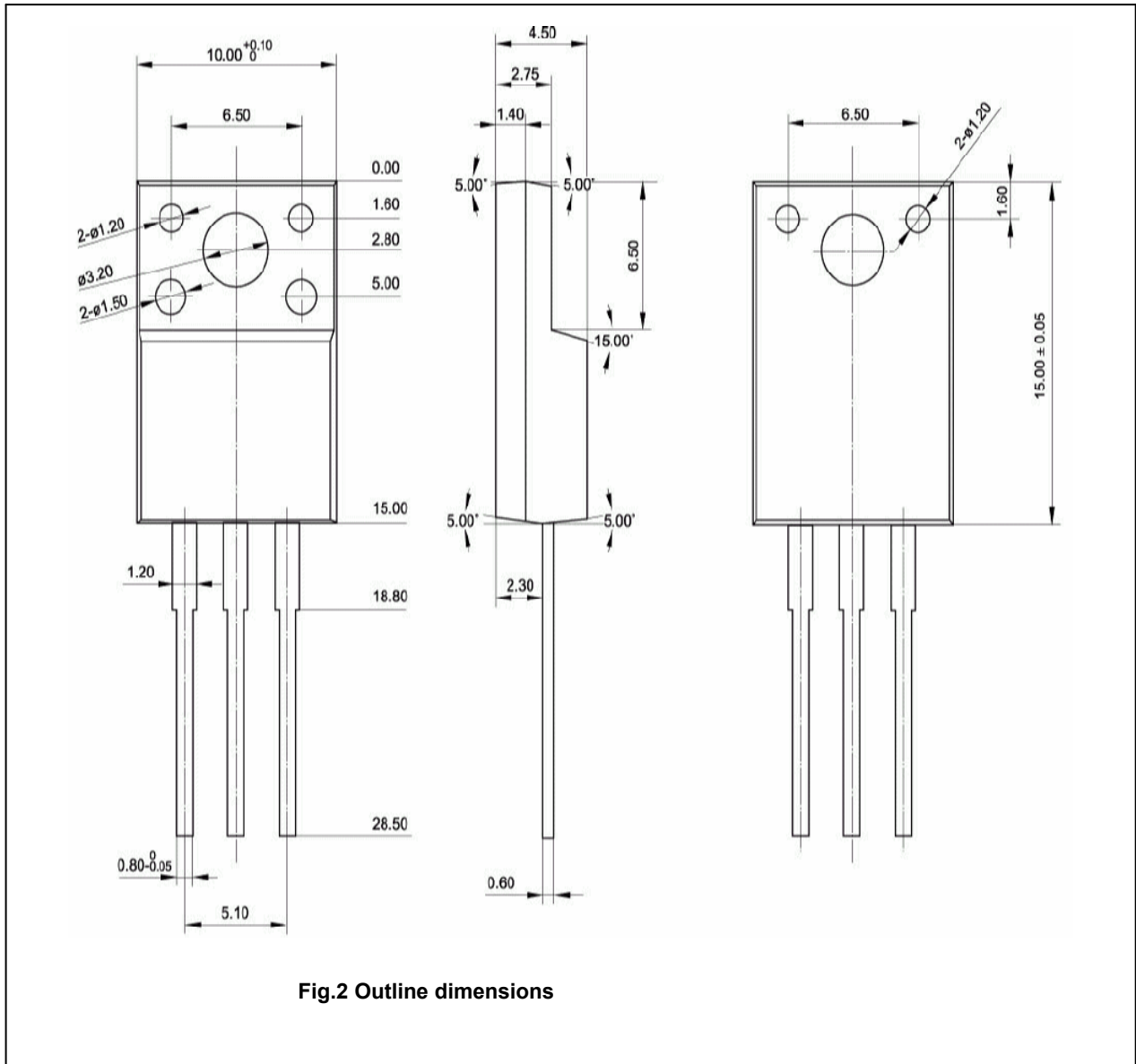


Fig.2 Outline dimensions